35. A method of forming an aluminum comprising line having a titanium nitride comprising layer thereon, the method comprising:

in a processing tool, physical vapor depositing a first layer comprising at least one of elemental aluminum or an aluminum alloy over a substrate in a first chamber, at least an outermost portion of the first layer being deposited at a first deposition temperature of at least 400°C;

after the first layer physical vapor depositing and without letting the outermost portion of the first layer cool from the first deposition temperature to a temperature below 360°C, physical vapor depositing at least one of elemental titanium or a titanium alloy on the first layer in a second chamber of the processing tool while at least an outer portion of the first layer is at a temperature of at least about 360°C, and forming therefrom a second layer comprising an alloy of titanium and the aluminum from the first layer in the second chamber during said depositing, the alloy having a higher melting point than that of the first layer, and wherein essentially all the physical vapor deposited titanium alloys with the aluminum of the first layer;

physical vapor depositing a third layer comprising titanium nitride on the second layer;

removing the substrate from the processing tool after depositing the third layer; and

forming first, second and third layers into a conductive line.

36. The method of claim 35 comprising depositing the second layer to have a thickness of from about 50 Angstroms to about 150 Angstroms.

37. The method of claim 35 comprising depositing the second layer to have a thickness of from about 100 Angstroms to about 200 Angstroms.

38. The method of claim 35 wherein the first layer consists essentially of elemental aluminum, an aluminum alloy, or a mixture thereof.

39. The method of claim 35 wherein the first layer consists essentially of elemental aluminum.

40. The method of claim 35 wherein the physical vapor depositing at least one of elemental titanium or a titanium alloy comprises physical vapor depositing elemental titanium.

41. The method of claim 35 wherein temperature of at least an outer portion of the first layer is at least about 360°C during the physical vapor depositing of the third layer.

42. The method of claim 35 wherein the third layer physical vapor depositing occurs in the second chamber of the processing tool.

43. The method of claim 35 wherein the physical vapor depositing of at least one of elemental titanium or a titanium alloy on the first layer in the second chamber of the processing tool comprises physical vapor depositing a titanium alloy layer, and forming therefrom a second layer comprising an alloy of titanium and the aluminum from the first layer in the second chamber during said depositing.

44. The method of claim 35 wherein the first deposition temperature is at least about 450°C.

45. The method of claim 35 wherein the first deposition temperature is greater than 450°C.

46. The method of claim 35 wherein after the first layer physical vapor depositing and before beginning the physical vapor depositing of the at least one of elemental titanium or titanium alloy, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

47. The method of claim 35 wherein the first deposition temperature is at least about 450°C, and wherein after the first layer physical vapor depositing and before beginning the physical vapor depositing of the at least one of elemental titanium or titanium alloy, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

48. The method of claim 35 wherein the first deposition temperature is greater than 450°C, wherein after the first layer physical vapor depositing and before beginning the physical vapor depositing of the at least one of elemental titanium or titanium alloy, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

49. (Amended) A method of forming an aluminum comprising line having a titanium nitride comprising layer thereon, the method comprising:

forming a first layer comprising at least one of elemental aluminum or an aluminum alloy over a substrate, at least an outermost portion of the first layer being formed at a first forming temperature of at least 400°C;

after forming the first layer and without letting the outermost portion of the first layer cool from the first forming temperature to a temperature below 360°C, forming a second layer by depositing titanium onto the first layer and forming therefrom during the depositing an alloy of titanium and the aluminum from the first layer, the alloy having a higher melting point than that of the first layer;

forming a third layer comprising titanium nitride over the second layer; and

forming the first, second and third layers into a conductive line.

50. The method of claim 49 wherein the first forming temperature is at least about 450°C.

51. The method of claim 49 wherein the first forming temperature is greater than 450°C.

52. The method of claim 49 wherein after forming the first layer and before depositing titanium, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

53. The method of claim 49 wherein the first forming temperature is at least about 450°C, and wherein after forming the first layer and before depositing titanium, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

54. The method of claim 49 wherein the first forming temperature is greater than 450°C, and wherein after forming the first layer and before depositing titanium, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

55. The method of claim 49 comprising forming the second layer to have a thickness of from about 50 Angstroms to about 150 Angstroms.

56. The method of claim 49 comprising forming the second layer to have a thickness of from about 100 Angstroms to about 200 Angstroms.

57. The method of claim 49 wherein the first layer consists essentially of elemental aluminum.

58. A method of forming an aluminum comprising line having a titanium nitride comprising layer thereon, the method comprising:

physical vapor depositing a first layer comprising at least one of elemental aluminum or an aluminum alloy over a substrate, at least an outermost portion of the first layer being deposited at a first deposition temperature of at least 400°C;

after the first layer physical vapor depositing and without letting the outermost portion of the first layer cool from the first deposition temperature to a temperature below 360°C, physical vapor depositing at least one of elemental titanium or a titanium alloy on the first layer and forming therefrom during the elemental titanium or titanium alloy depositing a second layer comprising an alloy of titanium and the aluminum from the first layer, the alloy having a higher melting point than that of the first layer;

physical vapor depositing a third layer comprising titanium nitride over the second layer; and

forming the first, second and third layers into a conductive line.

59. The method of claim 58 wherein the titanium nitride of the third layer is deposited in contact with the second layer.

60. The method of claim 58 wherein essentially all the physical vapor deposited titanium alloys with the aluminum of the first layer.

61. The method of claim 58 comprising physical vapor depositing each of the first layer, titanium, and third layer in different deposition chambers of the same processing tool.

62. The method of claim 58 comprising physical vapor depositing the titanium and third layer in the same deposition chamber.

63. The method of claim 58 comprising physical vapor depositing the first layer in two different chambers of the same processing tool, and physical vapor depositing the titanium and third layer in a common chamber of the same processing tool.

64. The method of claim 58 comprising physical vapor depositing the titanium and the third layer in the same deposition chamber without moving the substrate therefrom intermediate the titanium and third layer depositions.

65. The method of claim 58 wherein the first deposition temperature is at least about 450°C.

66. The method of claim 58 wherein the first deposition temperature is greater than 450°C.

67. The method of claim 58 comprising depositing the second layer to have a thickness of from about 50 Angstroms to about 150 Angstroms.

68. The method of claim 58 comprising depositing the second layer to have a thickness of from about 100 Angstroms to about 200 Angstroms.

69. The method of claim 58 wherein the first layer consists essentially of elemental aluminum, an aluminum alloy, or a mixture thereof.

70. The method of claim 58 wherein the first layer consists essentially of elemental aluminum.

71. The method of claim 58 wherein the physical vapor depositing at least one of elemental titanium or a titanium alloy comprises physical vapor depositing elemental titanium.

72. The method of claim 58 wherein after the first layer physical vapor depositing and before beginning the physical vapor depositing of the at least one of elemental titanium or titanium alloy, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

73. The method of claim 58 wherein the first deposition temperature is at least about 450°C, and wherein after the first layer physical vapor depositing and before beginning the physical vapor depositing of the at least one of elemental titanium or titanium alloy, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.

74. The method of claim 58 wherein the first deposition temperature is greater than 450°C, wherein after the first layer physical vapor depositing and before beginning the physical vapor depositing of the at least one of elemental titanium or titanium alloy, letting the outermost portion of the first layer cool from the first deposition temperature by 25°C or less.